Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C. This journal is © The Royal Society of Chemistry 2014

Supporting information

Stabilization and Tunable Microwave Dielectric Properties of Rutile Polymorph in α-PbO₂-Type GaTaO₄-Based Ceramics

Zhengwei Pan,¹ Xiaodi Yu,¹ Quanchao Wang,² Jiang Cao,¹ Fengjuan Pan,¹ Chaolun Liang,³ Fengqi

Lu,² Xiaojun Kuang,^{*, 2,1} Congxue Su², Jing Wang¹, Liang Fang^{*,2}

1. MOE Key Laboratory of Bioinorganic and Synthetic Chemistry, State Key Laboratory of

Optoelectronic Materials and Technologies, School of Chemistry and Chemical Engineering,

Sun Yat-Sen University, Guangzhou 510275, P. R. China

2. Guangxi Ministry-Province Jointly-Constructed Cultivation Base for State Key Laboratory of

Processing for Nonferrous Metal and Featured Materials, MOE Key Laboratory of New

Processing Technology for Nonferrous Metals and Materials, College of Materials Science and

Engineering, Guilin University of Technology, Guilin 541004 P. R. China

3. Instrumental Analysis and Research Center, Sun Yat-Sen University, Guangzhou 510275, P. R.

China

Thermal expansion of the monoclinic α -PbO₂-type GaTaO₄ from VT XRD data









Figure S1. The refined cell parameters of monoclinic GaTaO₄ from room temperature to 1000 °C.



Figure S2. XRD patterns of composition x = 0.075 in Ga_{1-x}Ta_{1-x}Ti_{2x}O₄ fired at 1300°C, 1350°C and

1400°C.



Figure S3. (a) Selected ED pattern for the α -PbO₂ phase in composition Ga_{0.925}Ta_{0.925}Ti_{0.15}O₄ (x = 0.075) along the [215] direction: the reflection condition is consistent with the monoclinic ordered P2c space group but violating the disordered Pbcn space group. (b) [100] projection of the ED pattern for the rutile phase Ga_{0.8}Ta_{0.8}Ti_{0.2}O₄ (x = 0.2).



Figure S4. SEM images of surface morphology of the $Ga_{1-x}Ta_{1-x}Ti_{2x}O_4$ ceramics (x = 0.3, 0.4) fired

at 1300°C.